Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	51	((257/76,77,136,192,264,328,330).CCLS.) and (heterostructure heterojunction) and @pd>"20041101"	US-PGPUB; USPAT	OR	ON	2005/06/14 13:59
L3	1	((US-20040079989-$).did.) and barrier adj forming and reception adj layer	US-PGPUB	OR	OFF	2005/06/14 13:59
L4	6	SiC with drift SAME drain and @pd>"20041101"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/14 13:59
L5	4	SiC with drift SAME drain and SiC and (polysilicon silicon) and source and @pd>"20041101"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/14 13:59
L6	9	SiC with drift and (silicon adj carbide SiC) and (polysilicon silicon) with (EPITAXY epitaxial) not "63" and @pd>"20041101"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/14 13:59
L7	7	("5923051" or "5,506,421") and @pd>"20041101"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/14 14:00

L8	12	(SiC with drift and (silicon adj carbide SiC) and (polysilicon silicon) with (EPITAXY epitaxial) not "63") and hetero$9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/14 14:00
L9	6	(JP-2002100773-$ US-6054352-$ us-6313487-$).did.	USPAT; JPO; DERWENT	OR	OFF	2005/06/14 14:01
L10	4	SiC with drift SAME drain and (silicon adj carbide SiC) and (polysilicon silicon) and source and @pd>"20041101"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/14 14:01
L11	103	baliga and @pd>"20041101"	US-PGPUB; USPAT	OR	OFF	2005/06/14 14:02
L12	18	baliga and SiC and @pd>"20041101"	US-PGPUB; USPAT	OR	OFF	2005/06/14 14:02
L13	123	(accufet accu-fet accumulation) and (SiC silicon adj carbide) and hetero$9 and @pd>"20041101"	US-PGPUB; USPAT	OR	OFF	2005/06/14 14:02
L14	27	(accufet accu-fet accumulation) and (SiC silicon adj carbide) and (heterojunction heterostructure) and @pd>"20041101"	US-PGPUB; USPAT	OR	OFF	2005/06/14 14:02
L15	4	(US-20040079989-$).did. or (US-5378912-$ or US-5753938-$ or US-5939754-$).did.	US-PGPUB; USPAT	OR	OFF	2005/06/14 14:02
L16	4	L15 and source adj electrode and drain adj electrode	US-PGPUB; USPAT	OR	OFF	2005/06/14 14:02

L17	0	SiC near3 drain and "5378912"	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/14 14:02
L18	41	SiC near3 drain and power near3 semiconductor	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/14 14:02
L19	39	SiC near3 drain and power near3 semiconductor and SiC and (si silicon poly polysilicon)	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/14 14:02
L20	0	SiC near3 drain and power near3 semiconductor and SiC and (si silicon poly polysilicon) near4 body	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/14 14:02
L21	9	SiC near3 drain and (si silicon poly polysilicon) near4 body	US-PGP UB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/14 14:02

L22	7	SiC near3 drain and (si silicon poly polysilicon) near4 body and gate adj (oxide insulat$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/14 14:02
L23	3	(("5929523") or ("6518197") or ("6737722")).PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/06/14 14:02
L24	127	SiC near3 drain	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/06/14 14:02
L25	1	("4,903,189").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/06/14 14:02
L26	1	(US-20040079989-$).did. or (US-5378912-$ or US-5753938-$ or US-5939754-$).did. and tunneling	US-PGPUB; USPAT	OR	OFF	2005/06/14 14:02
L27	4	Kaneko and hoshi and tunneling	US-PGPUB; USPAT	OR	OFF	2005/06/14 14:02
L28	51	("5378912" or "5753938" or "5939754") and (Sic silicon or gap or bandgap)	US-PGPUB; USPAT	OR	OFF	2005/06/14 14:02
L29	26	("5378912" or "5753938" or "5939754") and (Sic and silicon or gap or bandgap)	US-PGPUB; USPAT	OR	OFF	2005/06/14 14:02
L30	27	("5378912" or "5753938" or "5939754") and ((silicon adj carbide or Sic) and silicon or gap or bandgap)	US-PGPUB; USPAT	OR	OFF	2005/06/14 14:02